

Medium power transistor (60V, 2A)

2SC5866

- 1) High speed switching. (T_f : Typ. : 35ns at $I_c = 2A$)
- 2) Low saturation voltage, typically
(Typ. : 200mV at $I_c = 1.0A$, $I_B = 0.1A$)
- 3) Strong discharge power for inductive load and capacitance load.
- 4) Complements the 2SA2094

TSMT3

The drawing shows the mechanical specifications for the TSMT3 package. The top view is a rectangle with overall dimensions of 2.8 by 2.9. The lead pitch is 1.6, and the lead width is 0.4. The distance from the lead center to the package edge is 0.95. The side view shows a maximum height of 1.0, with a base thickness of 0.16, a lead height of 0.1, and a lead thickness of 0.05. The lead spacing is 0.3, and the lead width is 0.6.

(1)Base
(2)Emitter
(3)Collector

Each lead has same dimensions

Abbreviated symbol : VL

Low frequency amplifier
High speed switching

NPN Silicon epitaxial planar transistor

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SC5866		○

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
	I_{CP}	4	A ^{*1}
Power dissipation	P_C	500	mW ^{*2}
Junction temperature	T_j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C

*2 Each terminal mounted on a recommended land.

Transistor

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	60	—	—	V	$I_C=100\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	60	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	6	—	—	V	$I_E=100\mu A$
Collector cut-off current	I_{CBO}	—	—	1.0	μA	$V_{CB}=40V$
Emitter cut-off current	I_{EBO}	—	—	1.0	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	200	500	mV	$I_C=1A, I_B=0.1A$ *1
DC current gain	h_{FE}	120	—	390	—	$V_{CE}=2V, I_C=100mA$
Transition frequency	f_T	—	200	—	MHz	$V_{CE}=10V, I_E=-100mA, f=10MHz$ *1
Collector output capacitance	C_{ob}	—	10	—	pF	$V_{CB}=10V, I_E=0mA, f=1MHz$
Turn-on time	T_{on}	—	50	—	ns	$I_C=2A,$ $I_{B1}=200mA$
Storage time	T_{stg}	—	120	—	ns	$I_{B2}=-200mA$
Fall time	T_f	—	35	—	ns	$V_{CC}=25V$ *2

*1 Non repetitive pulse

*2 See switching characteristics measurement circuits

●hFE RANK

Q	R
120-270	180-390

●Electrical characteristic curves

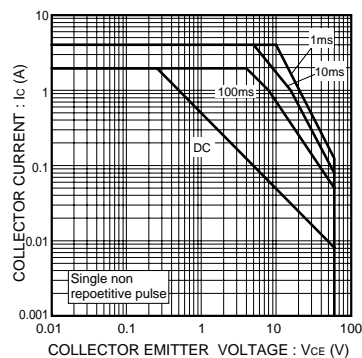


Fig.1 Safe operating area

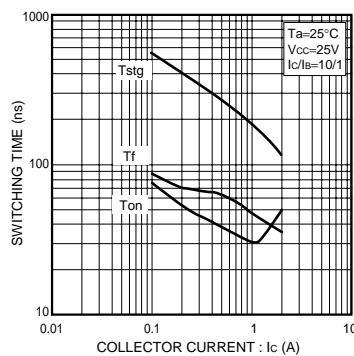


Fig.2 Switching Time

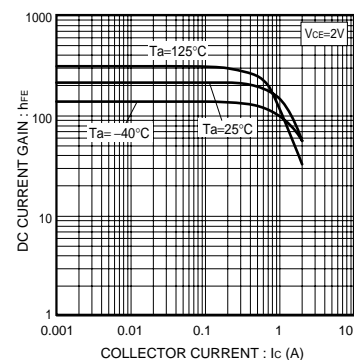


Fig.3 DC current gain vs. collector current

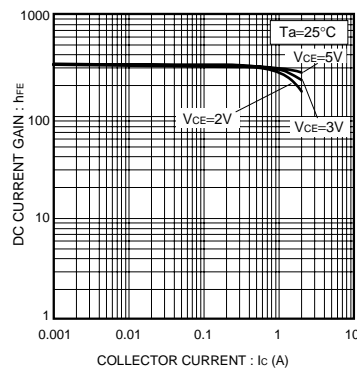


Fig.4 DC current gain vs. collector current

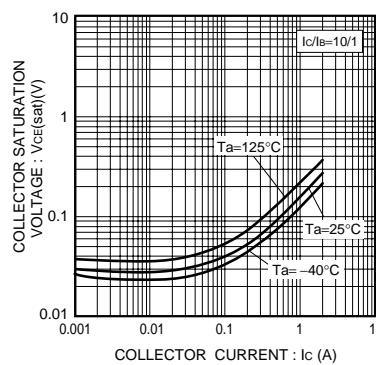


Fig.5 Collector-emitter saturation voltage vs. Collector Current

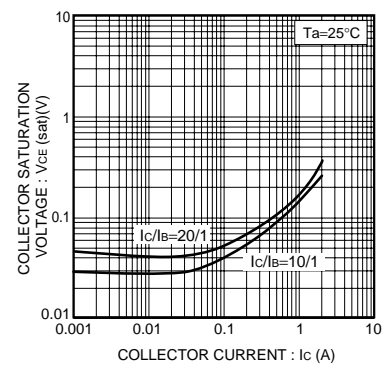


Fig.6 Collector-emitter saturation voltage vs. collector current

Transistor

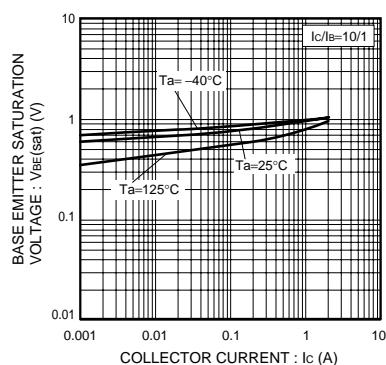


Fig.7 Base-emitter saturation voltage vs. collector current

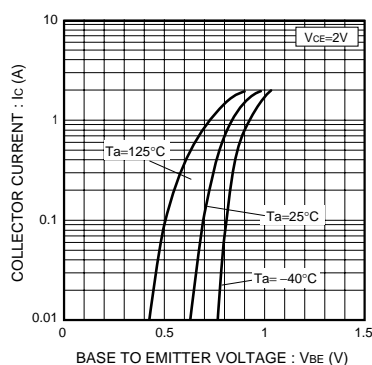


Fig.8 Ground emitter propagation characteristics

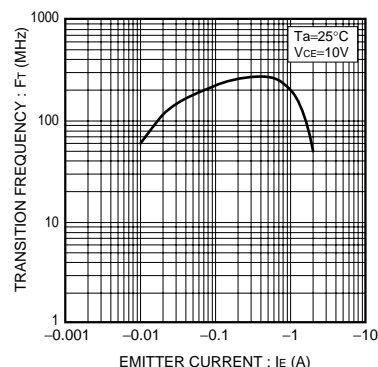


Fig.9 Transition frequency

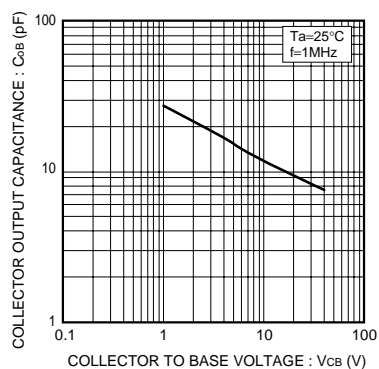
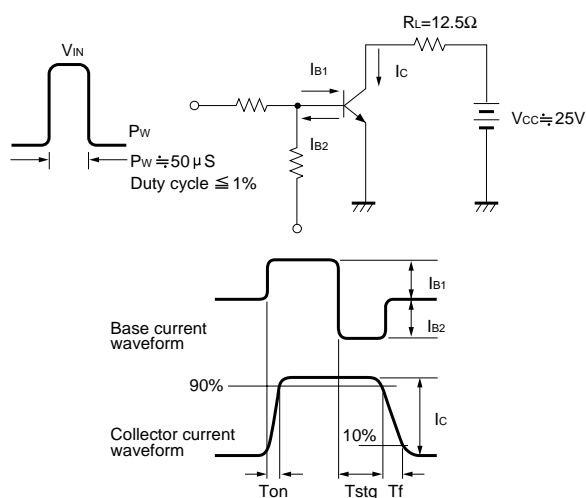


Fig.10 Collector output capacitance

●Switching characteristics measurement circuits



Appendix

Notes

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